

## IPP80P04P405AKSA1

#### IPP80P04P405AKSA1 Information



For Reference Only

Part Number IPP80P04P405AKSA1

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## IPP80P04P405AKSA1 Specifications

Manufacturer Part Number         IPP80P04P405AKSA1           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         Automotive, AEC-Q101, OptiMOS?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         151nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         10300pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         5.2 mOhm @ 80A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series Automotive, AEC-Q101, OptiMOS? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 151nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10300pF @ 25V Vgs (Max)  ### 20V FET Feature Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 5.2 mOhm @ 80A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case  TO-220-3	Manufacturer Part Number	IPP80P04P405AKSA1
Package         TO-220-3           Series         Automotive, AEC-Q101, OptiMOS?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         151nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         10300pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         5.2 mOhm @ 80A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3	Manufacturer	Infineon Technologies
Package         TO-220-3           Series         Automotive, AEC-Q101, OptiMOS?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         151nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         10300pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         5.2 mOhm @ 80A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3	Category	Discrete Semiconductor Products
SeriesAutomotive, AEC-Q101, OptiMOS?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs151nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs5.2 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         40V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         151nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         10300pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         5.2 mOhm @ 80A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs151nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs5.2 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Series	Automotive, AEC-Q101, OptiMOS?
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs151nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs5.2 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C       80A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       4V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       151nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       10300pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       125W (Tc)         Rds On (Max) @ Id, Vgs       5.2 mOhm @ 80A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3-1         Package / Case       TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs151nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs5.2 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs       151nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       10300pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       125W (Tc)         Rds On (Max) @ Id, Vgs       5.2 mOhm @ 80A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3-1         Package / Case       TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  5.2 mOhm @ 80A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs5.2 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	151nC @ 10V
FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 5.2 mOhm @ 80A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	10300pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  5.2 mOhm @ 80A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs5.2 mOhm @ 80A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Power Dissipation (Max)	125W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	5.2 mOhm @ 80A, 10V
Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO220-3-1
Report errors?	Package / Case	TO-220-3
		Report errors?

#### IPP80P04P405AKSA1 Guarantees



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### IPP80P04P405AKSA1 Payment Methods





















### IPP80P04P405AKSA1 Shipping Methods













If you have any question about IPP80P04P405AKSA1, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com